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Sommario/riassunto

This volume is the first in a series of three books addressing Electrostatic Discharge (ESD) physics, devices, circuits and design across the full range of integrated circuit technologies. ESD Physics and Devices provides a concise treatment of the ESD phenomenon and the physics of devices operating under ESD conditions. Voldman presents an accessible introduction to the field for engineers and researchers requiring a solid grounding in this important area. The book contains advanced CMOS, Silicon On Insulator, Silicon Germanium, and Silicon Germanium Carbon. In addition it also address
